

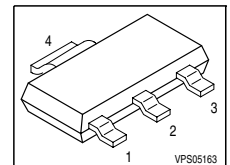
Cool MOS™ Power Transistor

Feature

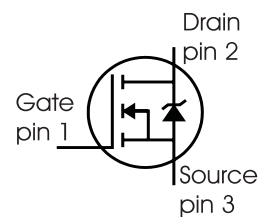
- New revolutionary high voltage technology
- Ultra low gate charge
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved transconductance

V_{DS}	600	V
$R_{DS(on)}$	3	Ω
I_D	0.4	A

SOT-223



Type	Package	Ordering Code	Marking
SPN02N60S5	SOT-223	Q67040-S4207	02N60S5



Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current $T_A = 25\text{ °C}$ $T_A = 70\text{ °C}$	I_D	0.4 0.3	A
Pulsed drain current, t_p limited by T_{jmax} $T_A = 25\text{ °C}$	$I_{D\text{ puls}}$	2.2	
Gate source voltage	V_{GS}	± 20	V
Gate source voltage AC ($f > 1\text{ Hz}$)	V_{GS}	± 30	
Power dissipation, $T_A = 25\text{ °C}$	P_{tot}	1.8	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	°C

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 480\text{ V}$, $I_D = 1.8\text{ A}$, $T_j = 125\text{ °C}$	dv/dt	20	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - soldering point	R_{thJS}	-	30	-	K/W
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ¹⁾	R_{thJA}	- - -	110 - -	-- 70	
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at $T_j=25\text{ °C}$ unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=0.25\text{ mA}$	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{ V}$, $I_D=1.8\text{ A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=80\text{ }\mu\text{A}$, $V_{GS}=V_{DS}$	3.5	4.5	5.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$, $T_j=150\text{ °C}$	- -	0.5 -	1 50	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$, $I_D=1.1\text{ A}$, $T_j=25\text{ °C}$ $T_j=150\text{ °C}$	- -	2.5 6.8	3 -	Ω

Electrical Characteristics , at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 0.3A$	-	0.5	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = 25V$, $f = 1MHz$	-	250	-	pF
Output capacitance	C_{oss}		-	110	-	
Reverse transfer capacitance	C_{rss}		-	8	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 350V$, $V_{GS} = 0/10V$, $I_D = 0.4A$, $R_G = 50\Omega$	-	30	-	ns
Rise time	t_r		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	110	-	
Fall time	t_f		-	30	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 350\text{V}$, $I_D = 0.4\text{A}$	-	1.8	-	nC
Gate to drain charge	Q_{gd}		-	4.5	-	
Gate charge total	Q_g	$V_{DD} = 350\text{V}$, $I_D = 0.4\text{A}$, $V_{GS} = 0\text{ to }10\text{V}$	-	7.4	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 350\text{V}$, $I_D = 0.4\text{A}$	-	8	-	V

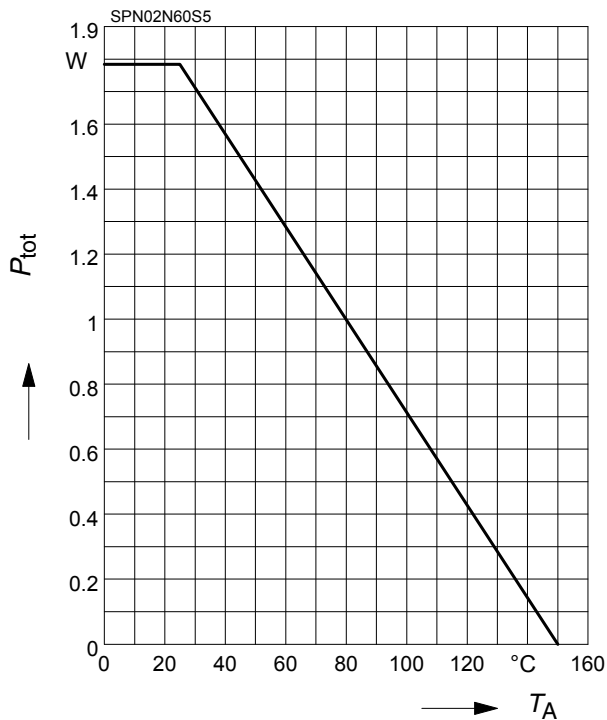
¹Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	$T_A = 25^{\circ}\text{C}$	-	-	0.4	A
Inverse diode direct current, pulsed	I_{SM}		-	-	2.2	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0\text{V}$, $I_F = I_S$	-	0.85	1.05	V
Reverse recovery time	t_{rr}	$V_R = 350\text{V}$, $I_F = I_S$, $di_F/dt = 100\text{A}/\mu\text{s}$	-	200	-	ns
Reverse recovery charge	Q_{rr}		-	0.7	-	μC

1 Power dissipation

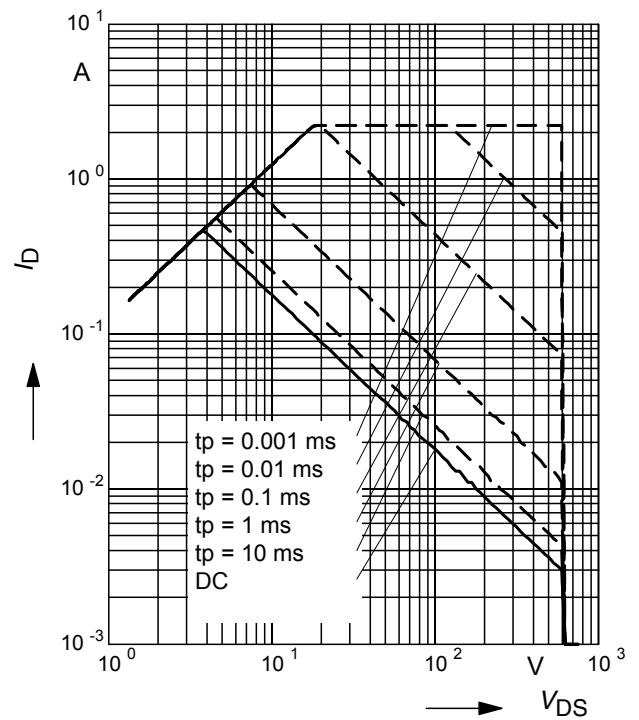
$$P_{\text{tot}} = f(T_A)$$



2 Safe operating area

$$I_D = f(V_{DS})$$

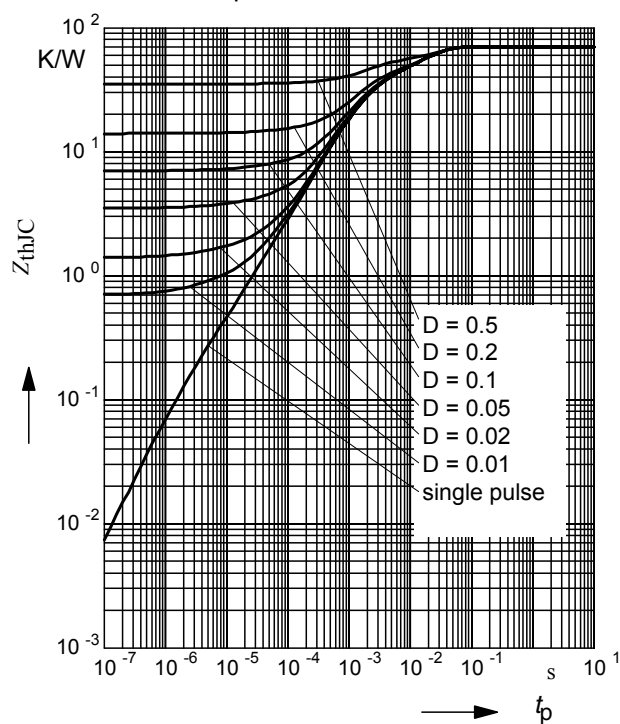
parameter : $D = 0$, $T_A = 25^\circ\text{C}$



3 Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

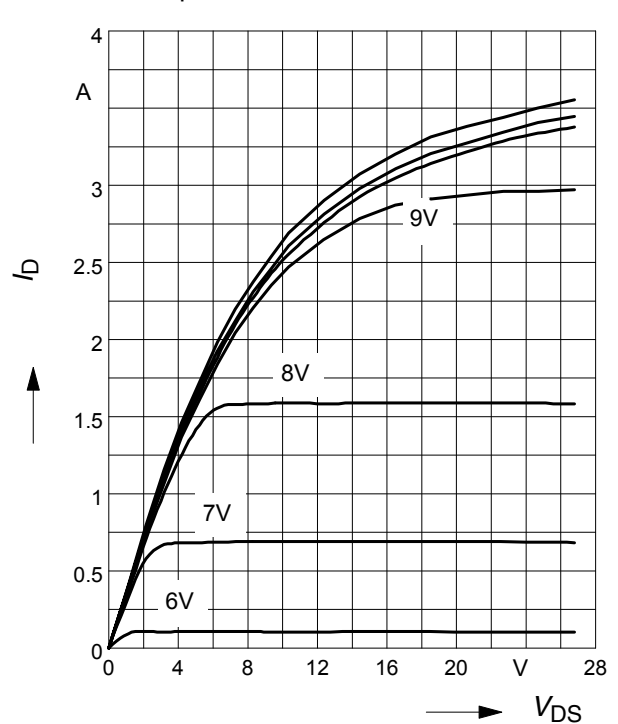
parameter: $D = t_p/T$



4 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

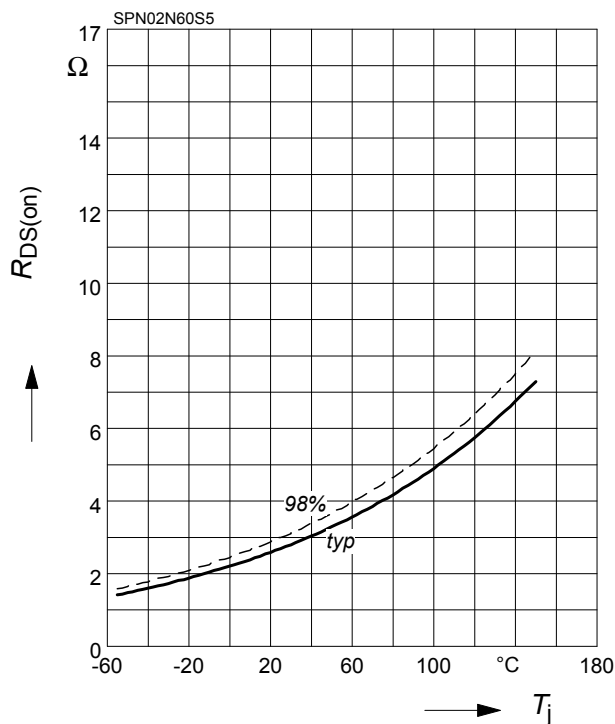
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



5 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

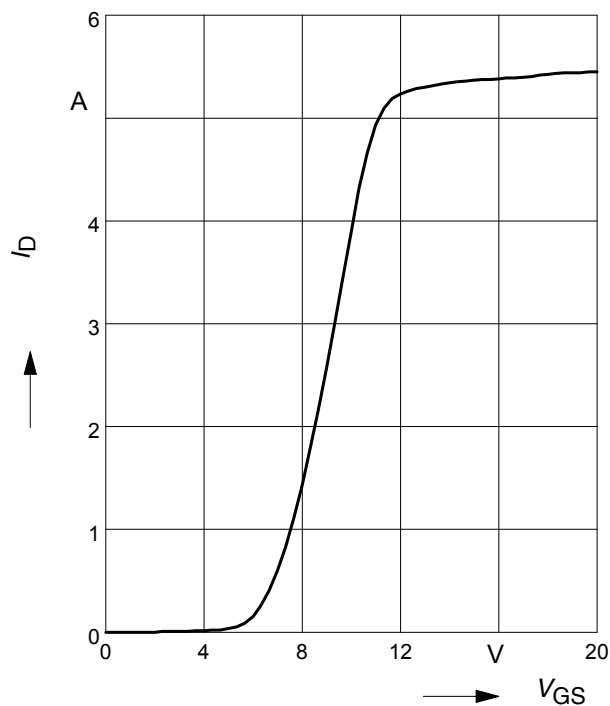
parameter: $I_D = 0.3 \text{ A}$, $V_{GS} = 10 \text{ V}$



6 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

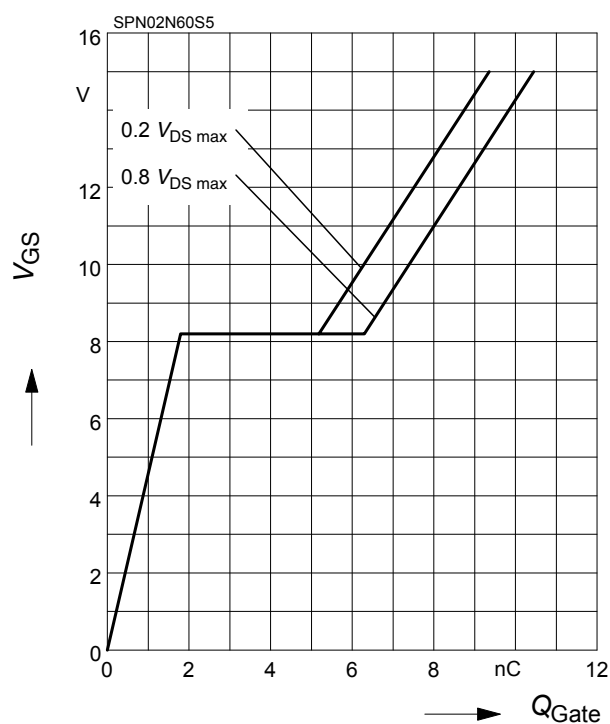
parameter: $t_p = 10 \mu\text{s}$



7 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

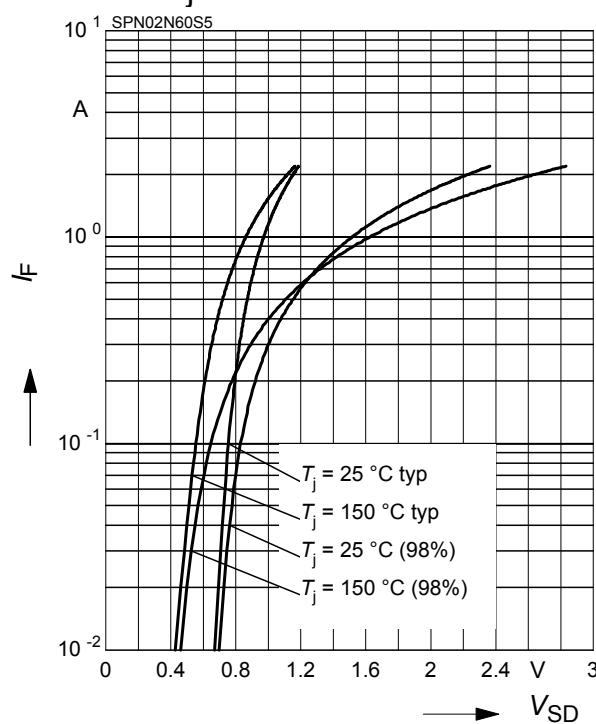
parameter: $I_D = 0.4 \text{ A}$ pulsed



8 Forward characteristics of body diode

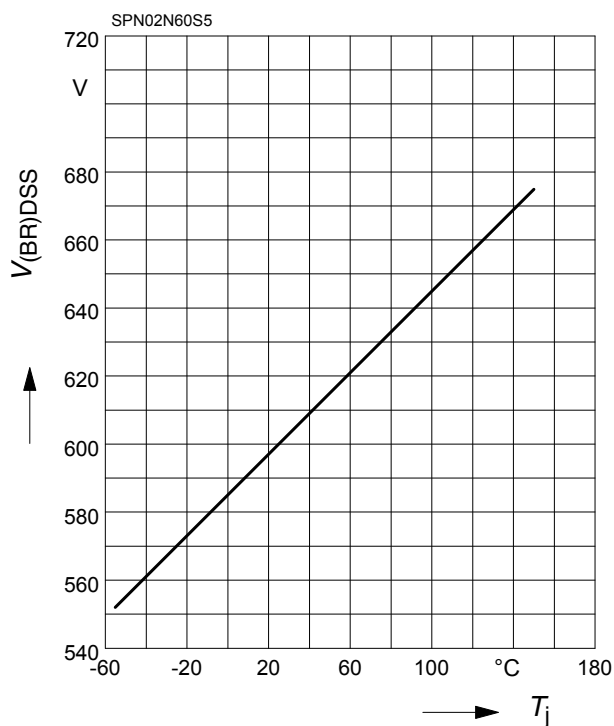
$$I_F = f(V_{SD})$$

parameter: T_j , $t_p = 10 \mu\text{s}$



9 Drain-source breakdown voltage

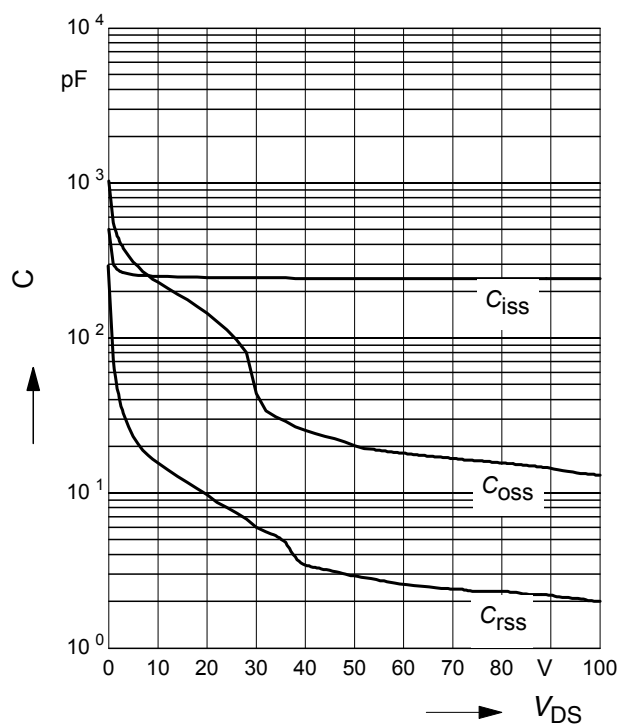
$$V_{(BR)DSS} = f(T_j)$$



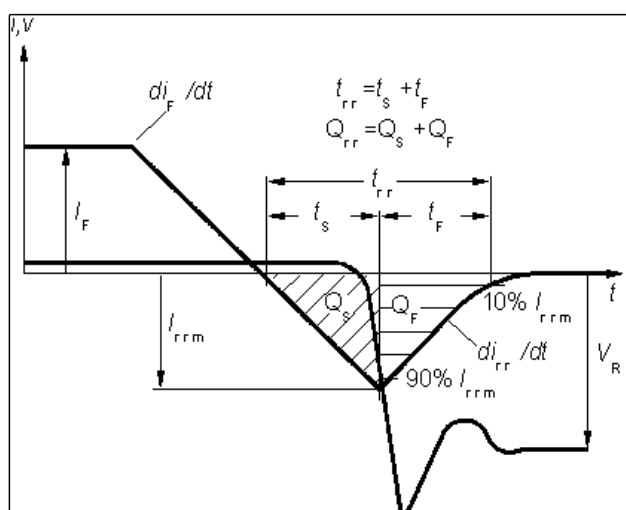
10 Typ. capacitances

$$C = f(V_{DS})$$

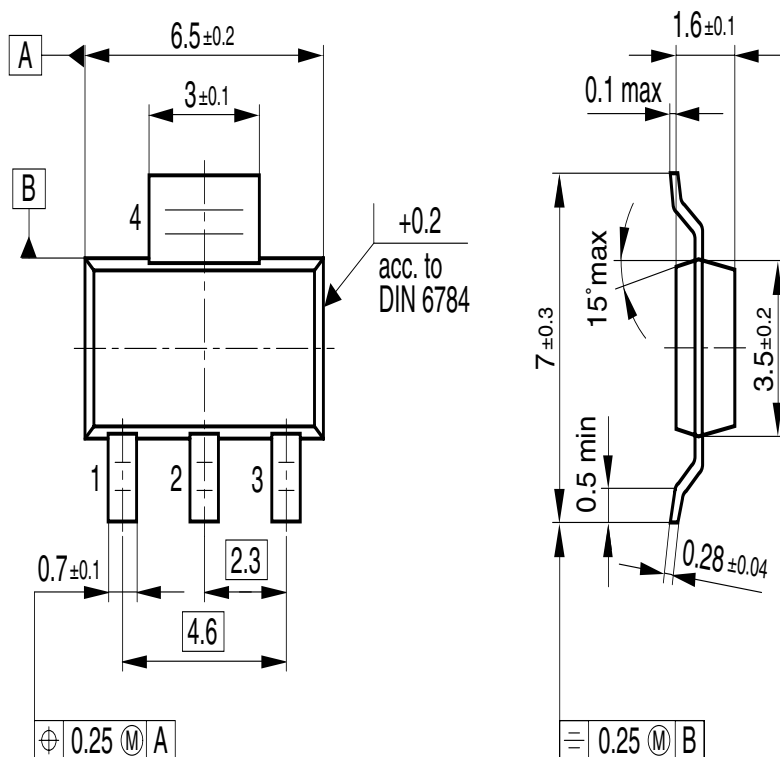
parameter: $V_{GS}=0V$, $f=1\text{ MHz}$



Definition of diodes switching characteristics



SOT223



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